



Figure 1 – High-resolution X-ray diffraction (HRXRD) scans of (a) 100 nm of AlGaSb capped with 30 nm of GaSb grown on a Zn:GaSb substrate (orange) and (b) 100 nm GaSbBi grown on an AlGaSb underlayer/Zn:GaSb substrate with matched growth conditions to the previous sample (blue). Scans shown were taken along the 004 crystallographic direction, while additional 224 reciprocal space maps (not shown) were taken to confirm the epilayers remained fully strained to the GaSb substrate.